ABSTRACT OF THE DISCLOSURE

There is provided an active matrix substrate which enables to shorten a fabrication process of a pixel electrode, improve exposure precision by self alignment, and prevent leakage failures between pixel electrodes. The active matrix substrate has TFTs disposed in the shape of a matrix. On a light permeable substrate, there are formed gate signal lines and capacity lines. On a gate insulating film on the lines, there are formed in sequence a semiconductor layer, a source electrode and a drain electrode separated right and left by a channel protection layer. Thus, the TFTs are fabricated. Then, the entire substrate is covered with an interlayer insulating film. On top of the interlayer insulating film, there are formed pixel electrodes, which are connected to the TFTs through contact holes piercing through the interlayer insulating film. The pixel electrodes are formed by applying on the interlayer insulating film a photosensitive transparent resin such as negative acrylic polymerized resin containing ITO, ATO or ZnO as transparent conductive particles, performing exposure from the back side of the substrate, and conducting development.